

Low Capacitance Bi-directional ESD Protection Diode

DESCRIPTION

The GESD05D6CU is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, portable devices, digital cameras, power supplies and many other portable applications where board space comes at a premium. Also because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed, VGA, DVI, SDI and other high speed line applications.

This device has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD (electrostatic discharge), and EFT (electrical fast transients).

FEATURES

♦ Transient protection for high-speed data line IEC 61000-4-2(ESD) ±8KV(Contact) ±15KV(Air)

Cable Discharge Event (CDE)

- ♦Peak power dissipation: 35W (8/20µs)
- ♦Protects one I/O line
- ♦Low clamping voltage
- ♦Working voltage: 5V
- ♦Low leakage current
- ♦Low capacitance

MACHANICAL DATA

- ♦DFN0603 package
- ♦ High temperature soldering guaranteed: 260°C/10s
- ♦Packaging: Tape and Reel
- ♦Reel size: 7 inch

ORDERING INFORMATION

Device: GESD05D6CUPackage: DFN0603

♦ Marking: Y

♦ Material: Halogen free and RoHS compliant

♦ Packing: Tape & Reel

♦ Quantity per reel: 15,000pcs

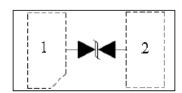
APPLICATIONS

- ♦ High Speed Line: USB1.0/2.0, VGA, DVI, SDI
- ♦ Serial and Parallel Ports
- ♦ Notebooks, Desktops, Servers
- ♦Projection TV
- ♦ Cellular handsets and accessories
- ♦Portable instrumentation
- ♦Peripherals

CIRCUIT DIAGRAM



PACKAGE OUTLINE





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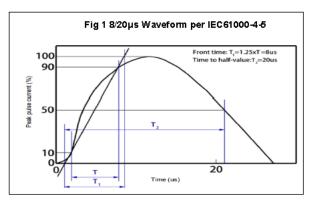
ABSOLUTE MAXIMUM RATING							
Symbol	Parameter	Value	Units				
V _{ESD}	ESD per IEC 61000-4-2 (Contact) ESD per IEC 61000-4-2 (Air)	±8 ±15	kV				
P _{PP}	Peak Pulse Power (8/20µs)	35	W				
Торт	Operating Temperature	-55~125	°C				
Тѕтс	Storage Temperature	-55~150	°C				

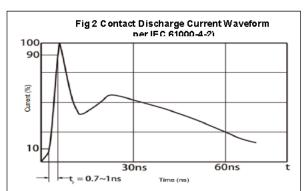
ELECTRICAL CHARACTERISTICS (Tamb=25°C)									
Symbol	Parameter	Test Condition	Min	Тур	Max	Units			
VRWM	Reverse Working Voltage				5.0	V			
V_{BR}	Reverse Breakdown Voltage	I _T = 1mA	5.6		9.4	V			
I _R	Reverse Leakage Current	V _{RWM} = 5V			2.0	μA			
Vc	Clamping Voltage	$I_{PP} = 1A, t_p = 8/20 \mu s$			10.5	V			
		$I_{PP} = 2A, t_p = 8/20 \mu s$			14.0	V			
V _{CTLP}	TLP Clamping Voltage	I_{PP} = 16A IEC61000-4-2 Level 4 equivalent (\pm 8kV Contact, \pm 15kV Air)		14.5		V			
RDYN	Dynamic Resistance	t⊳ = 100ns		0.3		Ω			
СJ	Junction Capacitance	V _R = 0V, f = 1MHz		3.0	4.5	pF			

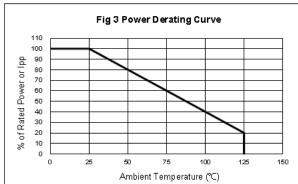


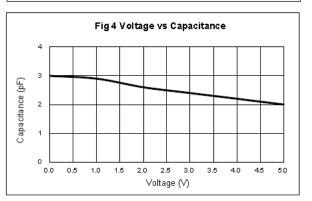
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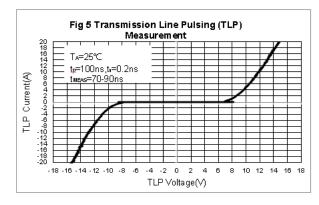
ELECTRICAL CHARACTERISTICS CURVE

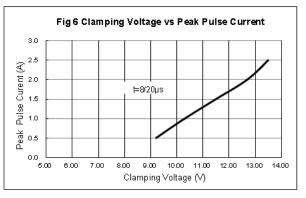








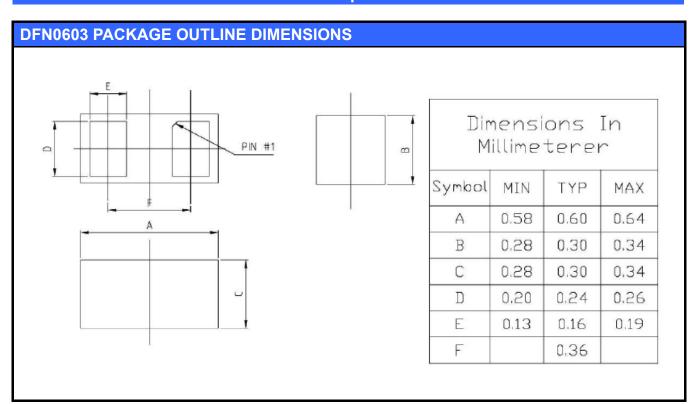




REV: D 3 of 4 www.gt-semi.com



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